

DMG204B0

Silicon NPN epitaxial planar type (Tr1)
 Silicon PNP epitaxial planar type (Tr2)

For low frequency amplification

■ Features

- Low collector-emitter saturation voltage $V_{CE(sat)}$
- Contributes to miniaturization of sets, reduction of component count.
- Eco-friendly Halogen-free package

■ Basic Part Number

DSC2001 + DSA2401 (Individual)

■ Packaging

Embossed type (Thermo-compression sealing): 3000 pcs / reel (standard)

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

	Parameter	Symbol	Rating	Unit
Tr1	Collector-base voltage (Emitter open)	V_{CBO}	60	V
	Collector-emitter voltage (Base open)	V_{CEO}	50	V
	Emitter-base voltage (Collector open)	V_{EBO}	7	V
	Collector current	I_C	100	mA
	Peak collector current	I_{CP}	200	mA
Tr2	Collector-base voltage (Emitter open)	V_{CBO}	-15	V
	Collector-emitter voltage (Base open)	V_{CEO}	-10	V
	Emitter-base voltage (Collector open)	V_{EBO}	-7	V
	Collector current	I_C	-0.5	A
	Peak collector current	I_{CP}	-1	A
Overall	Total power dissipation	P_T	300	mW
	Junction temperature	T_j	150	$^\circ\text{C}$
	Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

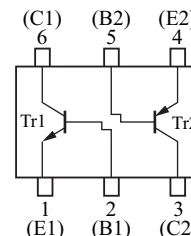
■ Package

- Code
Mini6-G4-B
- Pin Name

1: Emitter (Tr1)	4: Emitter (Tr2)
2: Base (Tr1)	5: Base (Tr2)
3: Collector (Tr2)	6: Collector (Tr1)

■ Marking Symbol: C4

■ Internal Connection



■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

• Tr1

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_{\text{C}} = 10 \mu\text{A}, I_{\text{E}} = 0$	60			V
Collector-emitter voltage (Base open)	V_{CEO}	$I_{\text{C}} = 2 \text{ mA}, I_{\text{B}} = 0$	50			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_{\text{E}} = 10 \mu\text{A}, I_{\text{C}} = 0$	7			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{\text{CB}} = 20 \text{ V}, I_{\text{E}} = 0$			0.1	μA
Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{\text{CE}} = 10 \text{ V}, I_{\text{B}} = 0$			100	μA
Forward current transfer ratio	h_{FE}	$V_{\text{CE}} = 10 \text{ V}, I_{\text{C}} = 2 \text{ mA}$	210		460	—
Collector-emitter saturation voltage	$V_{\text{CE(sat)}}$	$I_{\text{C}} = 100 \text{ mA}, I_{\text{B}} = 10 \text{ mA}$		0.13	0.3	V
Transition frequency	f_{T}	$V_{\text{CE}} = 10 \text{ V}, I_{\text{C}} = 2 \text{ mA}$		150		MHz
Collector output capacitance (Common base, input open circuited)	C_{ob}	$V_{\text{CB}} = 10 \text{ V}, I_{\text{E}} = 0, f = 1 \text{ MHz}$		1.5		pF

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

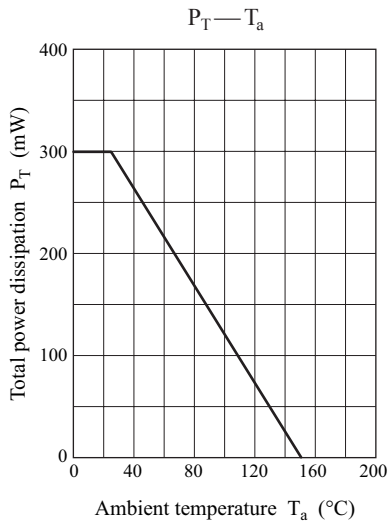
• Tr2

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_{\text{C}} = -10 \mu\text{A}, I_{\text{E}} = 0$	-15			V
Collector-emitter voltage (Base open)	V_{CEO}	$I_{\text{C}} = -1 \text{ mA}, I_{\text{B}} = 0$	-10			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_{\text{E}} = -10 \mu\text{A}, I_{\text{C}} = 0$	-7			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{\text{CB}} = -10 \text{ V}, I_{\text{E}} = 0$			-100	nA
Forward current transfer ratio *	h_{FE1}	$V_{\text{CE}} = -2 \text{ V}, I_{\text{C}} = -0.5 \text{ A}$	130		350	—
	h_{FE2}	$V_{\text{CE}} = -2 \text{ V}, I_{\text{C}} = -1 \text{ A}$	60			
Collector-emitter saturation voltage *	$V_{\text{CE(sat)}}$	$I_{\text{C}} = -0.4 \text{ A}, I_{\text{B}} = -8 \text{ mA}$		-0.15	-0.30	V
Base-emitter saturation voltage *	$V_{\text{BE(sat)}}$	$I_{\text{C}} = -0.4 \text{ A}, I_{\text{B}} = -8 \text{ mA}$		-0.8	-1.2	V
Transition frequency	f_{T}	$V_{\text{CE}} = -10 \text{ V}, I_{\text{C}} = -50 \text{ mA}$		250		MHz
Collector output capacitance (Common base, input open circuited)	C_{ob}	$V_{\text{CB}} = -10 \text{ V}, I_{\text{E}} = 0, f = 1 \text{ MHz}$		18		pF

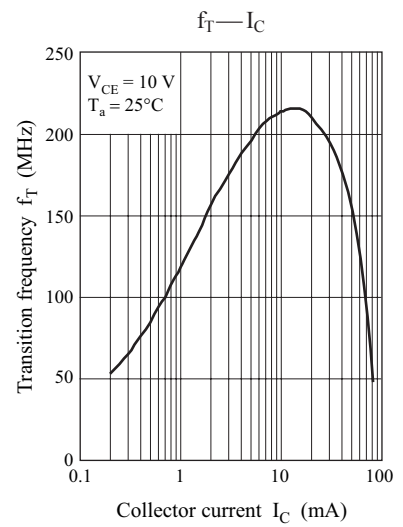
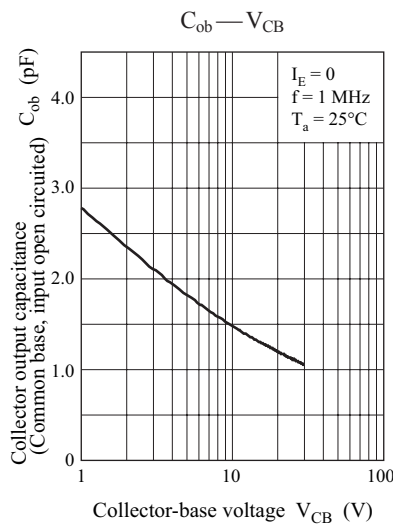
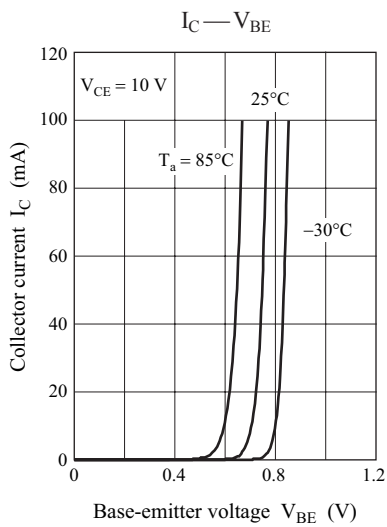
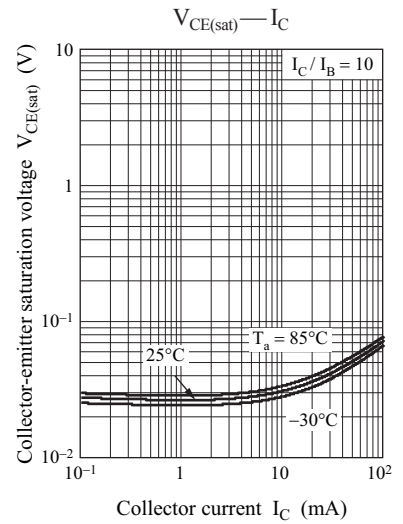
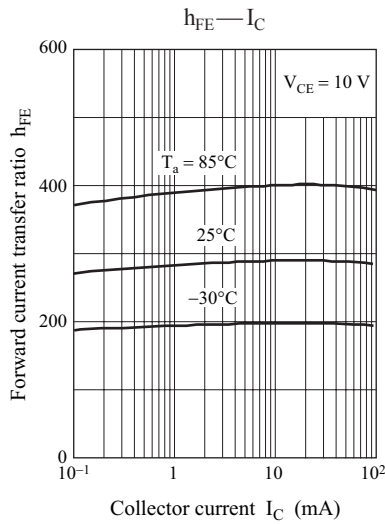
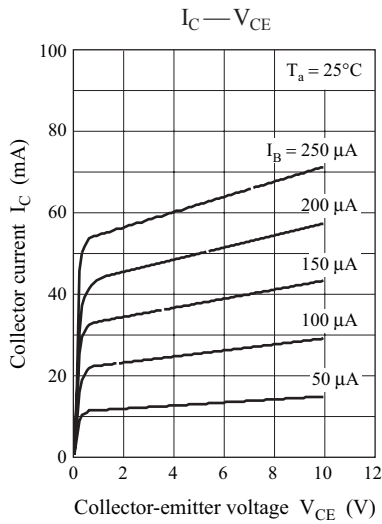
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2. *: Pulse measurement

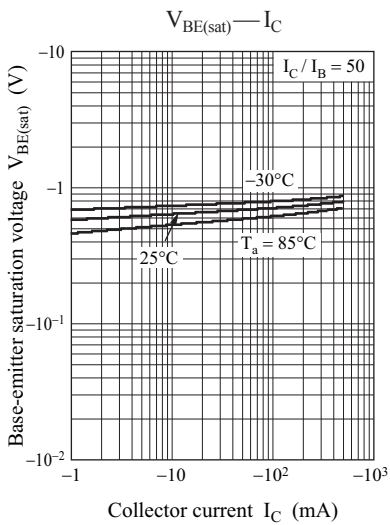
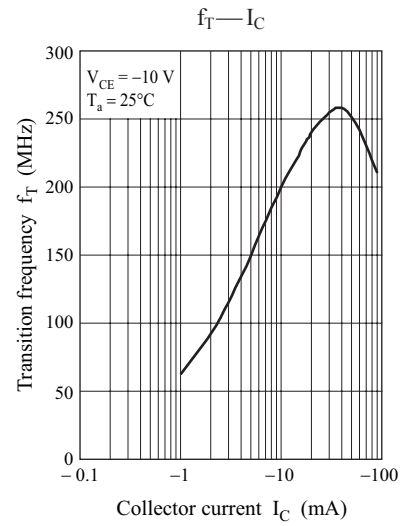
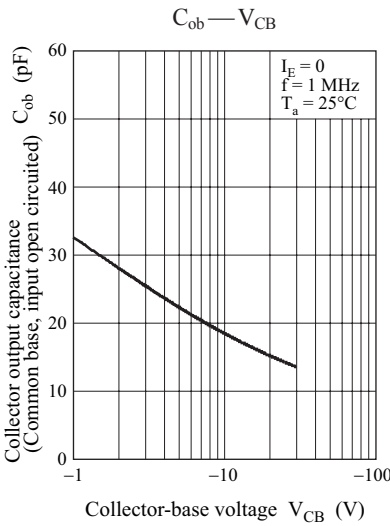
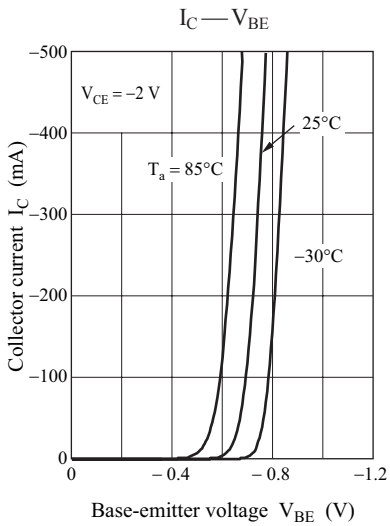
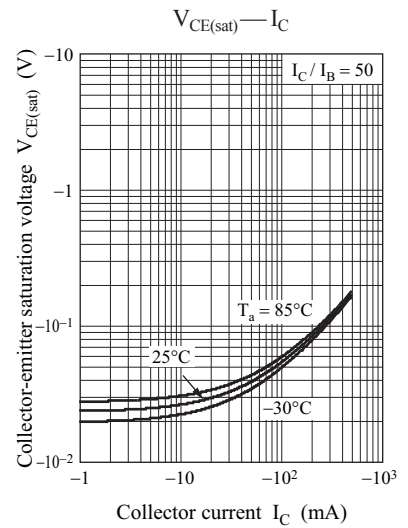
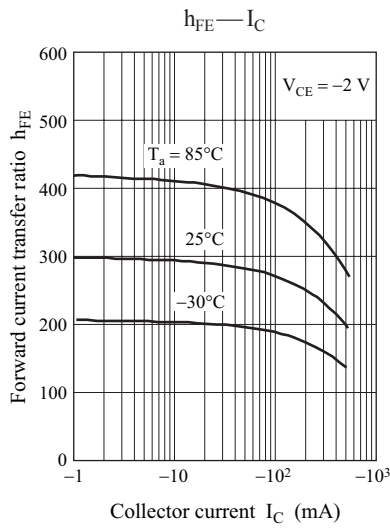
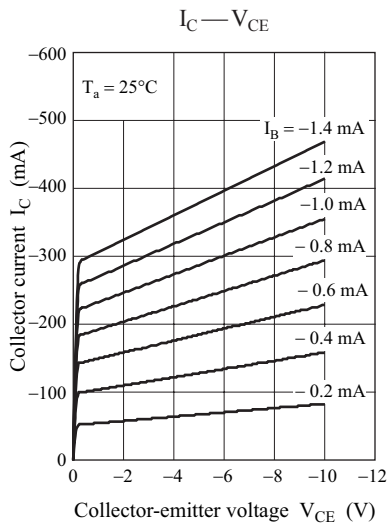
Common characteristics chart



Characteristics charts of Tr1

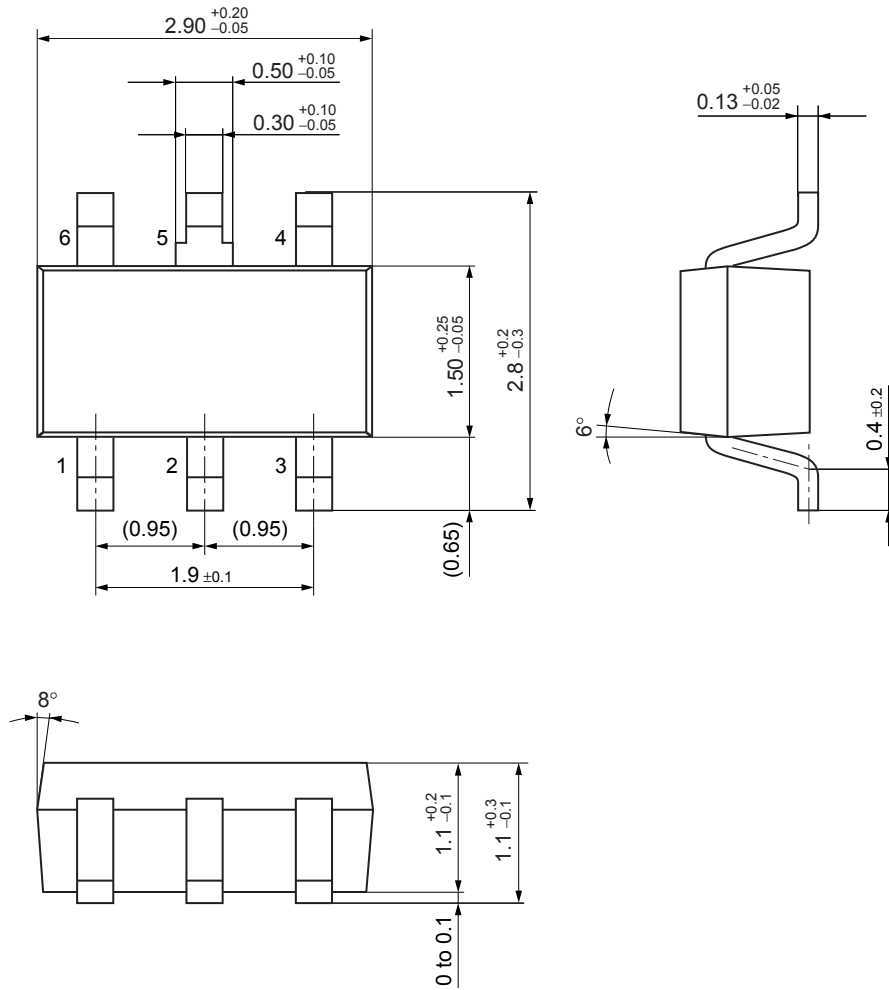


Characteristics charts of Tr2



Mini6-G4-B

Unit: mm



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